



IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Re the Application of: **GOTO, et al.**

Serial No.: 09/532,791

Filed: **March 22, 2000**

Group Art Unit: 2828

Examiner: T. NGUYEN

P.T.O. Confirmation No. 8585

For: **SEMICONDUCTOR LASER DEVICE AND METHOD OF FABRICATING THE SAME**

**AMENDMENT UNDER 37 CFR §1.111**

Commissioner for Patents  
Washington, D.C. 20231

January 15, 2003

Sir:

In response to the Office Action dated **July 25, 2002**, extended to **January 25, 2003** by a three-month Petition for Extension of Time, please amend the above-identified application as follows:

**IN THE CLAIMS:**

AMEND claims 1 and 11 to read as follows:

1. (Amended) A semiconductor laser device comprising:
- a first semiconductor layer including an active layer;
  - a striped second semiconductor layer formed on said first semiconductor layer; and
  - a current blocking layer formed on said first semiconductor layer on both sides of said second semiconductor layer,
- said second semiconductor layer including a cladding layer which comprises a lower layer having a first width at its lower end and an upper layer having a second width larger than said first

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